April 2013



FGAF20N60SMD 600 V, 20 A Field Stop IGBT

Features

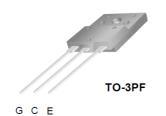
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.7 V(Typ.) @ I_C = 20 A
- High Input Impedance
- Fast Swiching: E_{OFF} = 7 uJ/A
- Tightened Parameter Distribution
- RoHS Compliant

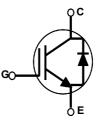
Applications

- Sewing Machine, CNC
- · Home Appliances, Motor-Control

General Description

Using novel field stop IGBT technology, Fairchild[®]'s new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		600	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
I _C	Collector Current	@ T _C = 25°C	40	A	
	Collector Current	@ T _C = 100 ^o C	20	A	
I _{CM (1)}	Pulsed Collector Current		60	A	
I _F	Diode Forward Current	@ T _C = 25°C	20	A	
'F	Diode Forward Current	@ T _C = 100 ^o C	10	A	
I _{FM (1)}	Pulsed Diode Maximum Forward Current		60	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	75	W	
• D	Maximum Power Dissipation	@ T _C = 100°C	37.5	W	
TJ	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
Τ _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	s	300	°C	

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

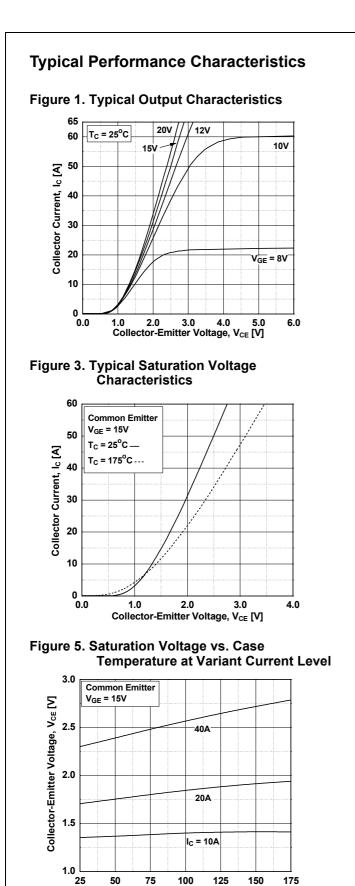
Symbo		Para	r		Ту	p.	Max.	Unit		
R _{eJC} (IGBT) Thermal Resistance, Junction to Ca			ise				2.0		°C/W	
$R_{\theta JC}(Diode)$ Thermal Resistance, Junction to Ca		ise		-	- 4.0		°C/W			
$R_{ extsf{ heta}JA}$	Ther	mal Resistance, Junctio	on to An	nbient		-	- 40		°C/W	
Package	e Mark	ing and Orderi	ing In	formatio	on					
Device N	larking	Device	Pa	ckage Reel Size		Таре	Tape Width		Quantity	
FGAF20N	60SMD	FGAF20N60SMD	٦	TO3-PF	-		-		30	
Electric	al Cha	racteristics of	the IC	GBT T _C = 25	5°C unless othe	rwise noted				
Symbol		Parameter		Test	Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	toristics									
BV _{CES}		to Emitter Breakdown \	Voltage	V _{GE} = 0V, I _C	; = 250μA		600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperat Voltage	ture Coefficient of Breal	kdown	V _{GE} = 0V, I _C = 250μA		-	0.62	-	V/ºC	
I _{CES}	Collector	Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0V$			-	-	250	μA
I _{GES}	G-E Leak	E Leakage Current $V_{GE} = V_{GES}, V_{CE} = 0V$, V _{CE} = 0V		-	-	±400	nA	
On Charact	teristics									
V _{GE(th)}	G-E Threshold Voltage			I_{C} = 250 μ A, V_{CE} = V_{GE}			3.5	4.7	6.0	V
- (- /	_			I _C = 20A, V _{GE} = 15V		-	1.7	-	V	
V _{CE(sat)}	Collector to Emitter Saturation Voltage		I _C = 20A, V _{GE} = 15V, T _C = 175 ^o C		-	1.9	-	V		
Dynamic C	haracteris	atics							1	
C _{ies}	Input Cap			V _{CE} = 30V, V _{GE} = 0V, f = 1MHz			-	925	-	pF
C _{oes}		apacitance					-	89	-	pF
C _{res}	Reverse	Transfer Capacitance					-	30	-	pF
Cuvita him a	0h awa at aw	i-4i						-		
Switching (Delay Time					_	12	_	ns
t _r	Rise Time	,		_			-	22	-	ns
t _{d(off)}		Delay Time		$V_{00} = 400V$	lo = 20A		-	91	-	ns
t _f	Fall Time	•		$V_{CC} = 400V, I_C = 20A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25$			-	21	27	ns
E _{on}	Turn-On	Switching Loss				°C	-	452	-	uJ
E _{off}	Turn-Off	Switching Loss					-	141	187	uJ
E _{ts}	Total Swit	tching Loss					-	593	-	uJ
t _{d(on)}	Turn-On	Delay Time		V _{CC} = 400V, I _C = 20A, R _G = 10Ω, V _{GE} = 15V,			-	12	-	ns
t _r	Rise Time	e					-	19	-	ns
t _{d(off)}	Turn-Off	Delay Time					-	93	-	ns
t _f	Fall Time					-00	-	16	-	ns
E _{on}	Turn-On	Switching Loss		Inductive Lo	ad, T _C = 17	5℃	-	667	-	uJ
E _{off}	Turn-Off	Switching Loss		1			-	317	-	uJ
E _{ts}	Total Swit	tching Loss		1			-	984	-	uJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge		-	64	-	nC
Q _{ge}	Gate to Emitter Charge	V _{CE} = 400V, I _C = 20A, V _{GE} = 15V	-	6.2	-	nC
Q _{gc}	Gate to Collector Charge	VGE - 15V	-	32	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Мах	Unit
V _{FM}	Diode Forward Voltage	I _F = 10A	T _C = 25°C	-	2.3	-	V
VFM Diode i ciwara voltage			T _C = 175 ^o C	-	1.67	-	
E _{rec}	Reverse Recovery Energy		T _C = 175 ^o C	-	13.8	-	uJ
t.	Diode Reverse Recovery Time	I _F =10A, dI _F /dt = 200A/μs	T _C = 25°C	-	26.7	-	ns
۲rr		$r_{\rm F} = 10$, $r_{\rm F}$ $r_{\rm C} = 200$ / μ s	T _C = 175 ^o C	-	88.2	-	110
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25 ^o C	-	42	-	nC
~II.	block hover to be house house		T _C = 175 ^o C	-	245	-	



Collector-EmitterCase Temperature, T_C [°C]

Figure 2. Typical Output Characteristics

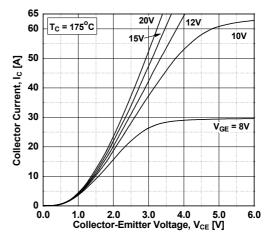


Figure 4. Transfer Characteristics

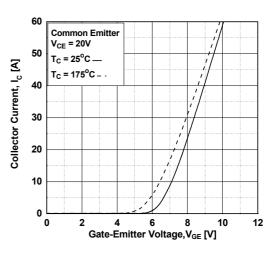
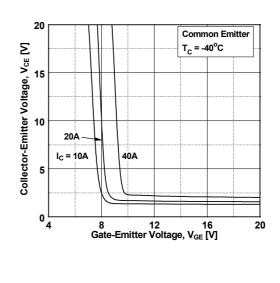


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

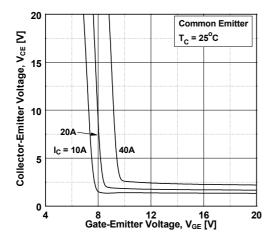


Figure 9. Capacitance Characteristics

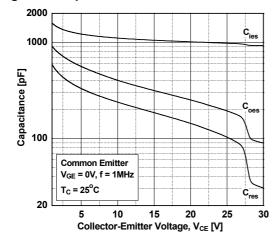


Figure 11. SOA Characteristics

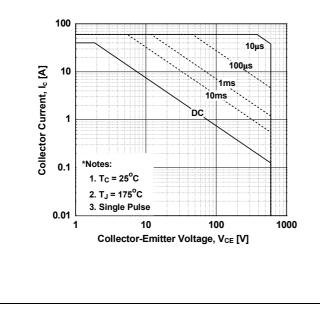


Figure 8. Saturation Voltage vs. V_{GE}

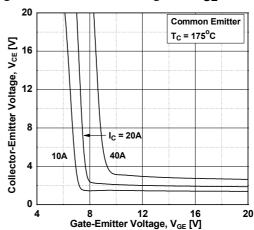


Figure 10. Gate charge Characteristics

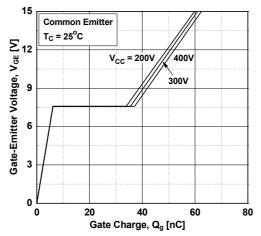
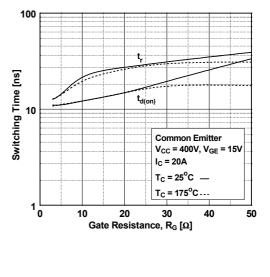


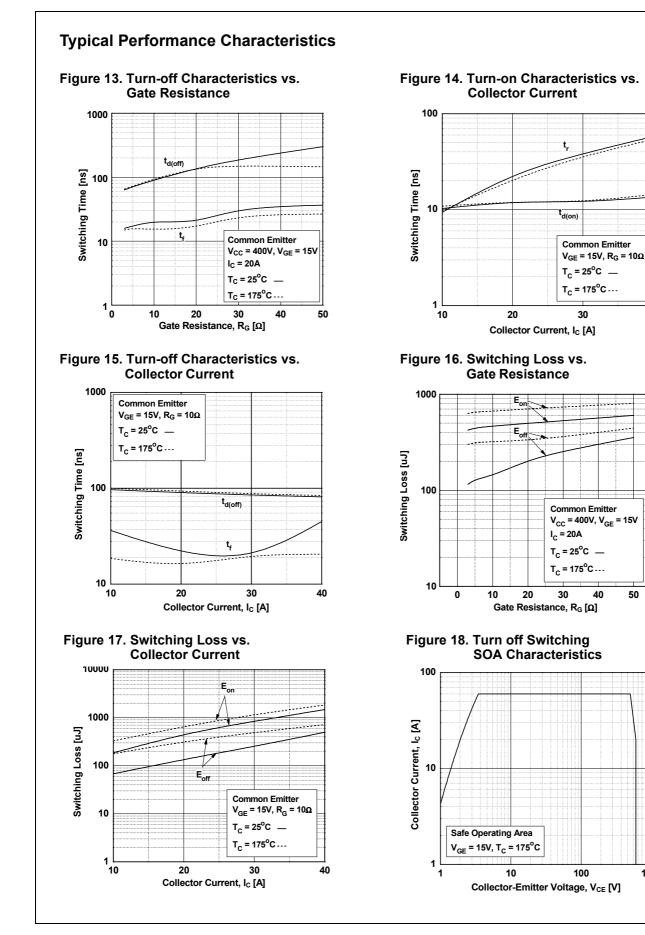
Figure 12. Turn-on Characteristics vs. Gate Resistance



FGAF20N60SMD 600 V 20 A Field Stop IGBT

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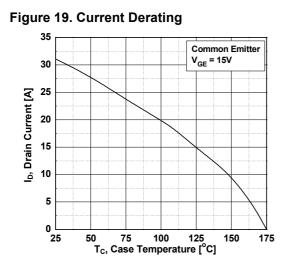
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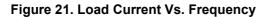


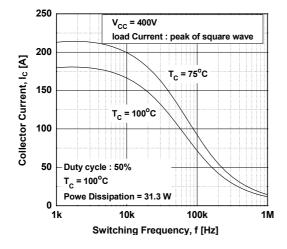
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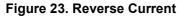
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Typical Performance Characteristics









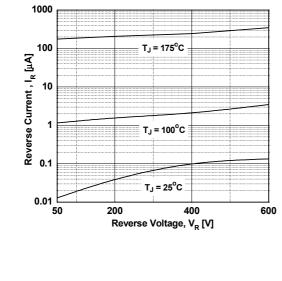


Figure 20. Power Dissipation

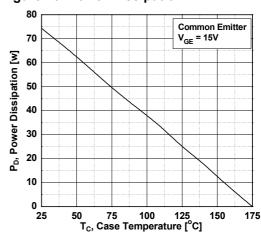
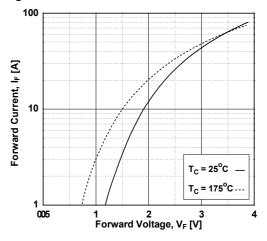
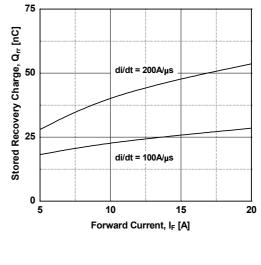
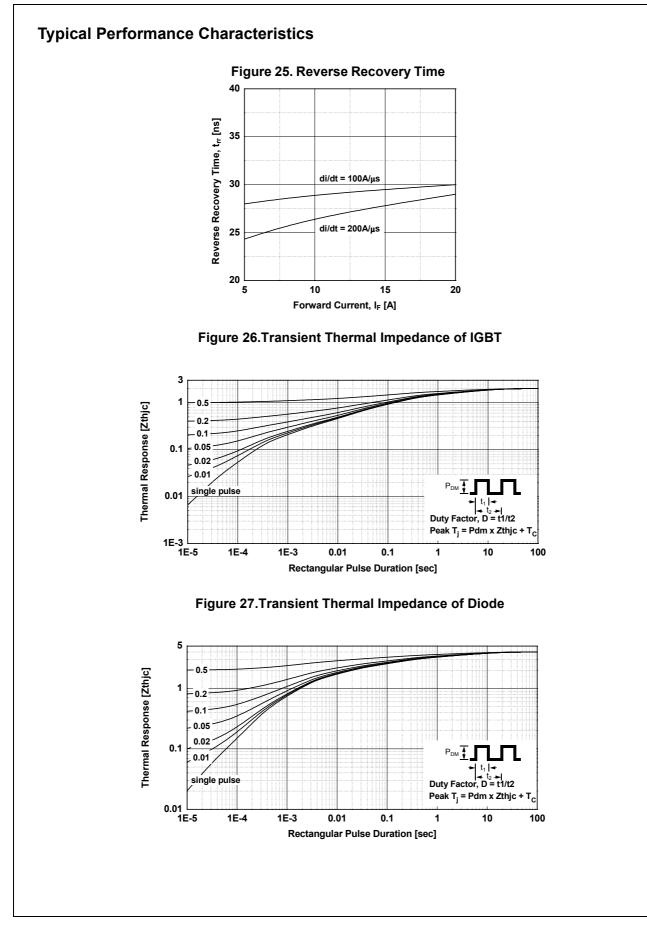


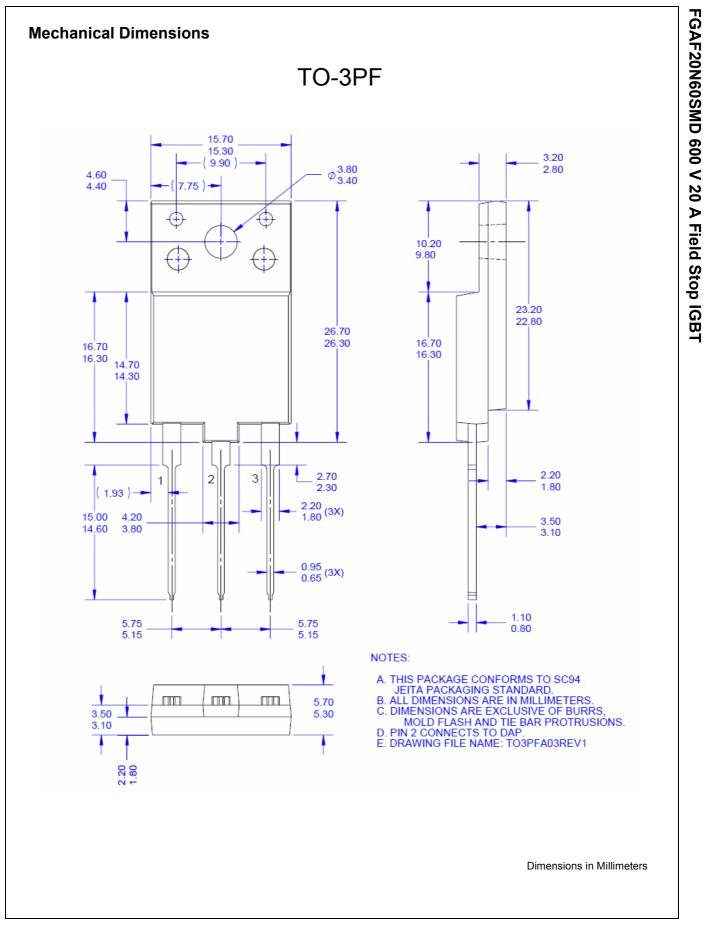
Figure 22. Forward Characteristics













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